

THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-IR6J-A73”

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 870 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=20mA		1.31	1.45	V
Reverse Voltage (Vr) IR=10uA	5			V
Radiated Power ¹⁾ (Po) IF=20mA	2.8			mW
Peak Wavelength (λp) IF=20mA	850	870	900	nm
Spectral Radiation Bandwidth (Δλ) IF=20mA		45		nm
Rise Time (Tr) IFp=500mA Tw=125ns,Duty=25%		20	35	ns
Fall Time (Tf) IFp=500mA Tw=125ns,Duty=25%		20	35	ns
PeakForward Voltage (Vf _m) IFp=400mA Tw=100us,Duty=10%		2.00	2.20	V

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

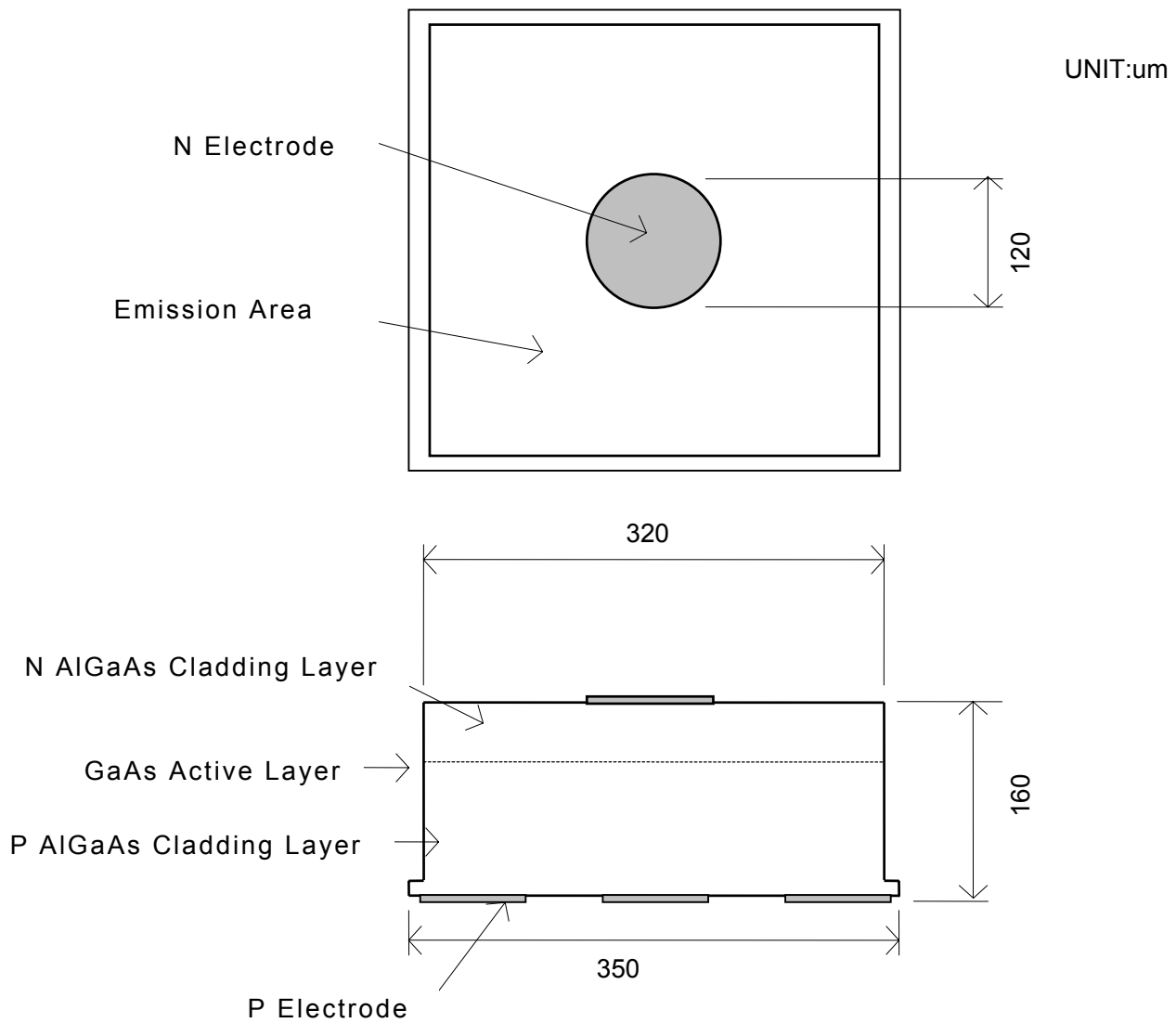
Continuous Maximum Forward Current	: 100 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Operating Temperature	: -30 to 85deg. C
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material	: AlGaAs
2)Structure	: Double Hetero Structure
3)Junction Size	: 0.320mm × 0.320mm
4)Thickness	: 0.160mm
5)Bond Pad Size	: 0.120mm diameter
6)Anode Metallization	: Gold Alloy
7)Cathode Metallization	: Gold Alloy

Physical Dimensions

Model YL-IR6J-A73



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.